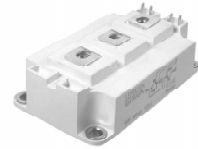


Absolute Maximum Ratings		Values	Units
Symbol	Conditions ¹⁾		
V _{CES}		1200	V
V _{CGR}	R _{GE} = 20 kΩ	1200	V
I _C	T _{case} = 25/85 °C	290 / 200	A
I _{CM}	T _{case} = 25/85 °C; t _p = 1 ms	580 / 400	A
V _{GES}		± 20	V
P _{tot}	per IGBT, T _{case} = 25 °C	1350	W
T _j , (T _{stg})		-40 ... +150 (125)	°C
V _{isol}	AC, 1 min.	2500	V
humidity	DIN 40040	Class F	
climate	DIN IEC 68 T.1	40/125/56	
Inverse Diode			
I _F = -I _C	T _{case} = 25/80 °C	195 / 130	A
I _{FM} = -I _{CM}	T _{case} = 25/80 °C; t _p = 1 ms	580 / 400	A
I _{FSM}	t _p = 10 ms; sin.; T _j = 150 °C	1450	A
I ² t	t _p = 10 ms; T _j = 150 °C	10 500	A ² s

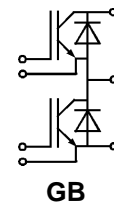
SEMITRANS® M Low Loss IGBT Modules

SKM 200 GB 124 D



SEMITRANS 3

Characteristics		min.	typ.	max.	Units
Symbol	Conditions ¹⁾				
V _{(BR)CES}	V _{GE} = 0, I _C = 4 mA	≥ V _{CES}	-	-	V
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 6 mA	4,5	5,5	6,5	V
I _{CES}	V _{GE} = 0 } T _j = 25 °C V _{CE} = V _{CES} } T _j = 125 °C	-	0,4	14	mA
I _{GES}	V _{GE} = 20 V, V _{CE} = 0	-	-	0,32	μA
V _{CESat}	I _C = 150 A } V _{GE} = 15 V; I _C = 200 A } T _j = 25 (125) °C	-	2,1(2,4)	2,45(2,85)	V
V _{CESat}	I _C = 200 A } T _j = 25 (125) °C	-	2,5(3,0)	-	V
g _{fs}	V _{CE} = 20 V, I _C = 150 A	62	-	-	S
C _{CHC}	per IGBT	-	-	700	pF
C _{ies}	V _{GE} = 0	-	11	15	nF
C _{oes}	V _{CE} = 25 V	-	1,6	2	nF
C _{res}	f = 1 MHz	-	0,8	1	nF
L _{CE}		-	-	20	nH
t _{d(on)}	V _{CC} = 600 V	-	75	-	ns
t _r	V _{GE} = -15 V / +15 V ³⁾	-	50	-	ns
t _{d(off)}	I _C = 150 A, ind. load	-	520	-	ns
t _f	R _{Gon} = R _{Goff} = 7Ω	-	50	-	ns
E _{on}	T _j = 125 °C	-	21	-	mWs
E _{off}		-	19	-	mWs
Inverse Diode ⁸⁾					
V _F = V _{EC}	I _F = 150 A } V _{GE} = 0 V; I _F = 200 A } T _j = 25 (125) °C	-	2,0(1,8)	2,5	V
V _F = V _{EC}	I _F = 200 A } T _j = 25 (125) °C	-	2,25(2,05)	-	V
V _{TO}	T _j = 125 °C ²⁾	-	1,1	1,2	V
r _t	T _j = 125 °C ²⁾	-	-	7	mΩ
I _{RRM}	I _F = 150 A; T _j = 125 °C ²⁾	-	78	-	A
Q _{rr}	I _F = 150 A; T _j = 125 °C ²⁾	-	19,5	-	μC
Thermal characteristics					
R _{thjc}	per IGBT	-	-	0,09	°C/W
R _{thjc}	per diode	-	-	0,25	°C/W
R _{thch}	per module	-	-	0,038	°C/W



Features

- MOS input (voltage controlled)
- N channel, homogeneous Silicon structure NPT-IGBT (Non punch through)
- Low saturation voltage
- Low inductance case
- Low tail current with low temperature dependence
- High short circuit capability, self limiting to 6 * I_{Cnom}
- Latch-up free
- Fast & soft inverse CAL diodes ⁸⁾
- Isolated copper baseplate using DCB Direct Copper Bonding Technology without hard mould
- Large clearance (12 mm) and creepage distances (20 mm)

Typical Applications → B 6 – 161

- Switching (not for linear use)
- Inverter drives
- UPS

¹⁾ T_{case} = 25 °C, unless otherwise specified

²⁾ I_F = -I_C, V_R = 600 V, -di_F/dt = 1500 A/μs, V_{GE} = 0 V

³⁾ Use V_{GEoff} = -5... -15 V

⁸⁾ CAL = Controlled Axial Lifetime Technology

Cases and mech. data → B 6 – 162

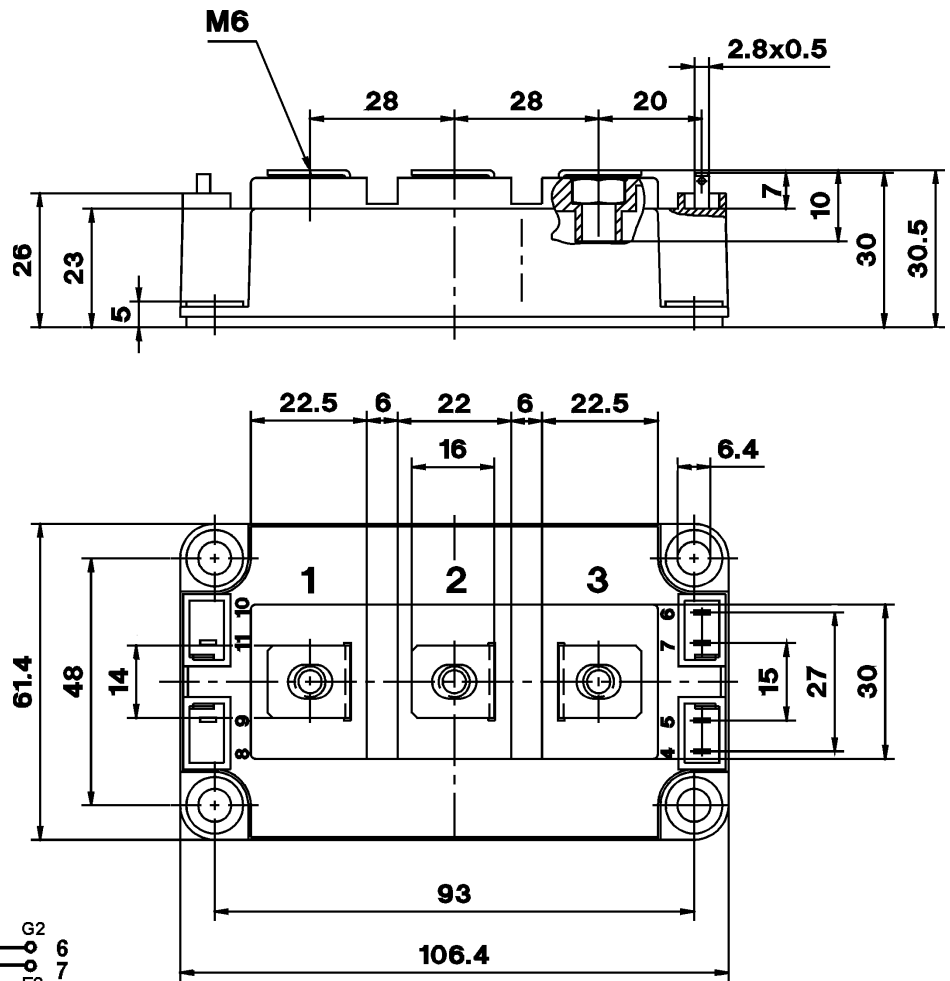
SEMITRANS 3

Case D 56

UL Recognized

File no. E 63 532

SKM 200 GB 124 D



Dimensions in mm

Case outline and circuit diagram

Mechanical Data			Values			Units
Symbol	Conditions		min.	typ.	max.	
M ₁	to heatsink, SI Units	(M6)	3	—	5	Nm
	to heatsink, US Units		27	—	44	lb.in.
M ₂	for terminals, SI Units	(M6)	2,5	—	5	Nm
	for terminals, US Units		22	—	44	lb.in.
a			—	—	5x9,81	m/s ²
w			—	—	325	g

This is an electrostatic discharge sensitive device (ESDS). Please observe the international standard IEC 747-1, Chapter IX.

Three devices are supplied in one SEMIBOX A without mounting hardware, which can be ordered separately under Ident No. 33321100 (for 10 SEMITRANS 3). Larger packing units of 12 and 20 pieces are used if suitable
 Accessories → B 6 – 4.
 SEMIBOX → C – 1.